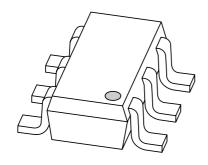
DISCRETE SEMICONDUCTORS

DATA SHEET



BC817DPNNPN/PNP general purpose transistor

Product data sheet Supersedes data of 2002 Aug 09



NPN/PNP general purpose transistor

BC817DPN

FEATURES

- High current (500 mA)
- 600 mW total power dissipation
- Replaces two SOT23 packaged transistors on same PCB area.

APPLICATIONS

- · General purpose switching and amplification
- · Complementary driver
- Half and full bridge driver.

DESCRIPTION

NPN/PNP transistor pair in a SOT457 (SC-74) plastic package.

MARKING

TYPE NUMBER	MARKING CODE	
BC817DPN	N4	

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V _{CEO}	collector-emitter voltage	45	V
I _C	collector current (DC)	500	mA
I _{CM}	peak collector current	1	Α

PINNING

PIN	DESCRIPTION		
1, 4	emitter	TR1; TR2	
2, 5	base	TR1; TR2	
6, 3	collector	TR1; TR2	

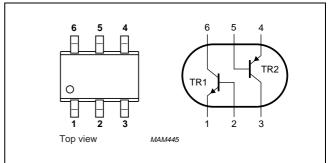


Fig.1 Simplified outline (SOT457) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transis	Per transistor; for the PNP transistor with negative polarity				
V _{CBO}	collector-base voltage	open emitter	_	50	V
V _{CEO}	collector-emitter voltage	open base	_	45	V
V _{EBO}	emitter-base voltage	open collector	_	5	V
I _C	collector current (DC)		_	500	mA
I _{CM}	peak collector current		_	1	Α
I _{BM}	peak base current		_	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	370	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C
Per device)	-	•	•	•
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	600	mW

Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm².

NPN/PNP general purpose transistor

BC817DPN

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	208	K/W

Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm².

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

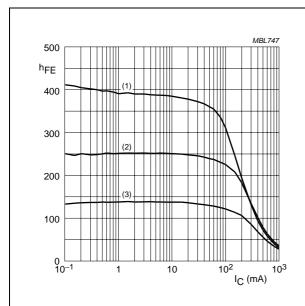
SYMBOL	PARAMETER CONDITIONS		MIN.	TYP.	MAX.	UNIT
Per transis	Per transistor unless otherwise specified; for the PNP transistor with negative polarity					
I _{CBO}	collector-base cut-off current	V _{CB} = 20 V; I _E = 0	_	_	100	nA
		V _{CB} = 20 V; I _E = 0; T _j = 150 °C	_	_	5	μА
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0	_	_	100	nA
h _{FE}	DC current gain	V _{CE} = 1 V; I _C = 100 mA; note 1	160	_	400	
		V _{CE} = 1 V; I _C = 500 mA; note 1	40	_	_	
V _{CEsat}	collector-emitter saturation voltage	I _C = 500 mA; I _B = 50 mA; note 1	_	_	700	mV
V _{BE}	base-emitter voltage	$V_{CE} = 1 \text{ V; } I_{C} = 500 \text{ mA;}$ notes 1 and 2	_	_	1.2	V
NPN trans	NPN transistor					
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	_	5	_	pF
f _T	transition frequency	V _{CE} = 5 V; I _C = 10 mA; f = 100 MHz	100	_	-	MHz
PNP transistor						
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	_	9	_	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA};$ f = 100 MHz	80	_	-	MHz

Notes

- 1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$
- 2. V_{BE} decreases by approximately -2 mV/K with increasing temperature.

NPN/PNP general purpose transistor

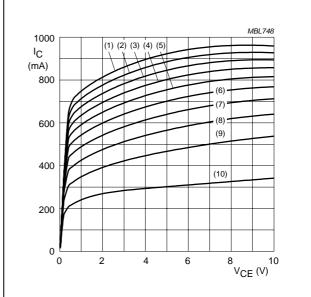
BC817DPN



TR1 (NPN) V_{CE} = 1 V.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.2 DC current gain as a function of collector current; typical values.



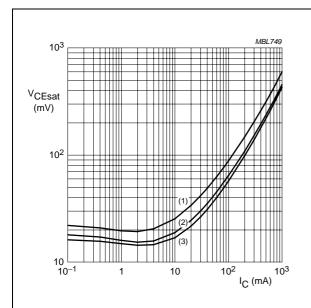
TR1 (NPN)

- (1) $I_B = 15 \text{ mA}.$
- (5) $I_B = 9 \text{ mA}$.
- (9) $I_B = 3 \text{ mA}.$ (10) $I_B = 1.5 \text{ mA}$.
- (2) $I_B = 13.5 \text{ mA}$. (6) $I_B = 7.5 \text{ mA}$. (3) $I_B = 12 \text{ mA}.$
 - (7) $I_B = 6 \text{ mA}.$
- (8) $I_B = 4.5 \text{ mA}.$ (4) $I_B = 10.5 \text{ mA}.$

Fig.3 Collector current as a function of collector-emitter voltage; typical values.

NPN/PNP general purpose transistor

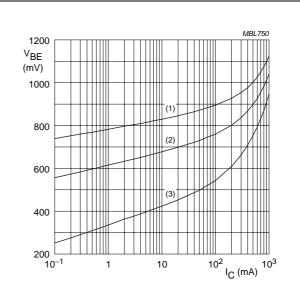
BC817DPN



TR1 (NPN) $I_{C}/I_{B} = 10$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



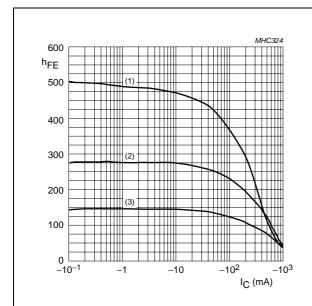
TR1 (NPN) V_{CE} = 1 V.

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) T_{amb} = 150 °C.

Fig.5 Base-emitter voltage as a function of collector current; typical values.

NPN/PNP general purpose transistor

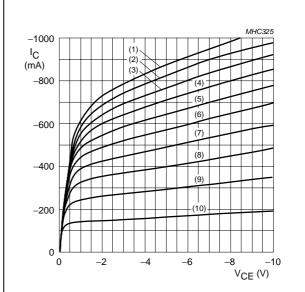
BC817DPN



TR2 (PNP) $V_{CE} = -1 V$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.6 DC current gain as a function of collector current; typical values.



TR2 (PNP)

6

(1) $I_B = -7 \text{ mA}$.

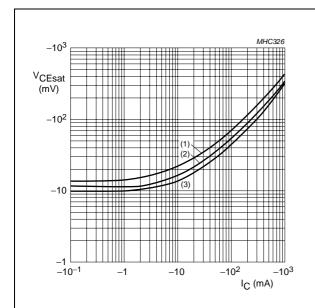
(4) $I_B = -4.9 \text{ mA}$.

- (5) $I_B = -4.2 \text{ mA}.$
- (9) $I_B = -1.4 \text{ mA}.$ (10) $I_B = -0.7 \text{ mA}.$
- (2) $I_B = -6.3 \text{ mA}.$ (3) $I_B = -5.6 \text{ mA}.$
- (6) $I_B = -3.5 \text{ mA}.$ (7) $I_B = -2.8 \text{ mA}.$
- (8) $I_B = -2.1 \text{ mA}.$

Fig.7 Collector current as a function of collector-emitter voltage; typical values.

NPN/PNP general purpose transistor

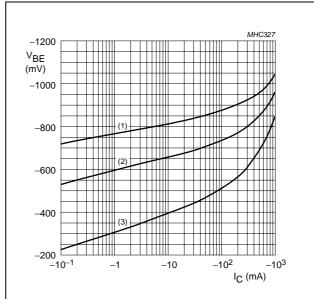
BC817DPN



TR2 (PNP) $I_C/I_B = 10$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.8 Collector-emitter saturation voltage as a function of collector current; typical values.



TR2 (PNP) $V_{CE} = -1 \text{ V}.$

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

Fig.9 Base-emitter voltage as a function of collector current; typical values.

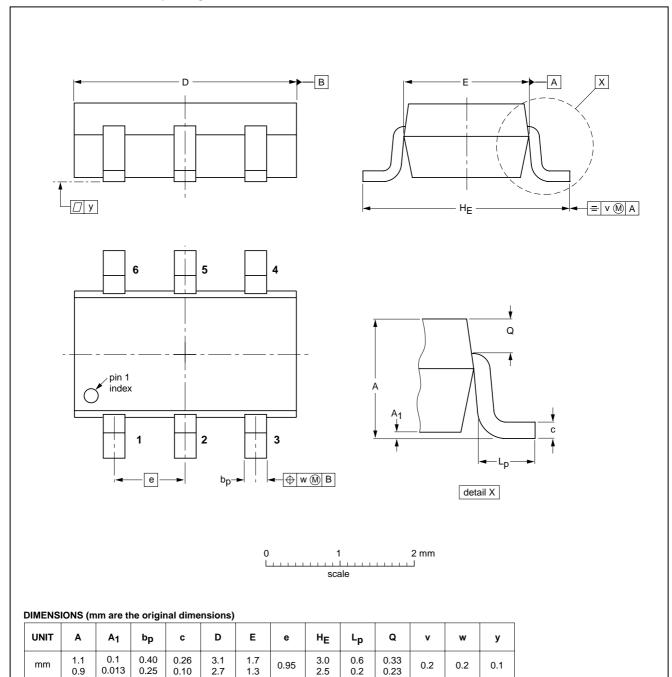
NPN/PNP general purpose transistor

BC817DPN

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT457



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT457			SC-74			97-02-28 01-05-04

2002 Nov 22 8

0.9

0.013

0.25

NPN/PNP general purpose transistor

BC817DPN

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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Printed in The Netherlands 613514/02/pp10 Date of release: 2002 Nov 22 Document order number: 9397 750 10583

